NSN 5961-01-214-9673

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Inclosure Material:

Metal

Overall Length:

1.550 inches

Overall Height:

0.300 inches

Overall Width:

1.050 inches

Mounting Facility Quantity:

2

Internal Configuration:

Junction contact-darlington connected

Joint Electronic Device Engineering Council/jedec/case Outline Designation:

To-3

Mounting Method:

Unthreaded hole

Features Provided:

Hermetically sealed case

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

500.0 collector-to-emitter, with voltage between base and emitter and 450.0 collector-to-emitter substaining voltage, with specified circuit between base and emitter and 400.0 collector-to-emitter, substaining voltage, base open-circuited and 8.0 emitter to base voltage, instantaneous

Current Rating Per Characteristic:

10.00 amperes source cutoff current and 2.50 amperes source cutoff current

Power Rating Per Characteristic:

150.0 watts small-signal input power, common-collector absolute

Transfer Ratio:

30.0 static forward current transfer ratio, common-emitter and 300.0 static forward current transfer ratio, common-emitter

Maximum Operating Tempurature Per Measurement Point:

200.0 degrees celsius junction

Special Features:

Junction pattern arrangement: npn

Terminal Type And Quantity:

2 pin and 1 case

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

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